

GSM8968

100V N-Channel Enhancement Mode MOSFET

Product Description

GSM8968, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

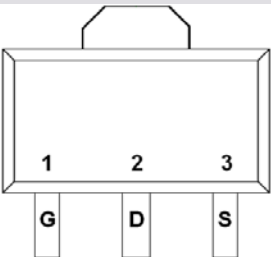
Features

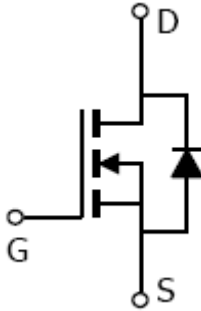
- 100V/3.0A, $R_{DS(ON)}=300m\Omega@V_{GS}=10V$
- 100V/2.0A, $R_{DS(ON)}=310m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- SOT-89-3L package design

Applications

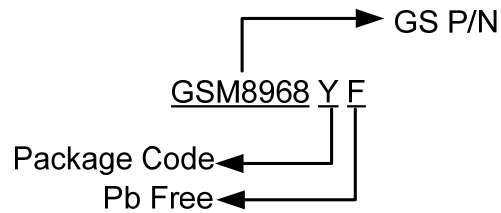
- Motor and Load Control
- Power Management in White LED System
- Push Pull Converter
- LCD TV Inverter & AD/DC Inverter Systems.

Packages & Pin Assignments

GSM8968YF(SOT-89-3L)	
	
Pin	Description
1	Gate
2	Drain
3	Source

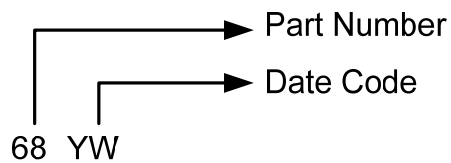


Ordering Information



Part Number	Package	Quantity Reel
GSM8968YF	SOT-89-3L	1000 PCS

Marking Information



Absolute Maximum Ratings

$T_A=25^\circ\text{C}$ Unless otherwise noted

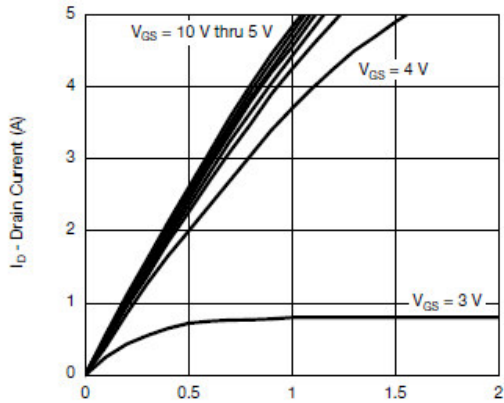
Symbol	Parameter	Typical	Unit	
V_{DSS}	Drain-Source Voltage	100	V	
V_{GSS}	Gate –Source Voltage	± 20	V	
I_D	Continuous Drain Current($T_J=150^\circ\text{C}$)	$T_A = 25^\circ\text{C}$	3.0	A
		$T_A = 70^\circ\text{C}$	2.0	
I_{DM}	Pulsed Drain Current	6	A	
I_S	Continuous Source Current(Diode Conduction)	1.6	A	
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	1.45	W
		$T_A = 70^\circ\text{C}$	0.6	
T_J	Operating Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	120	$^\circ\text{C}/\text{W}$	

Electrical Characteristics

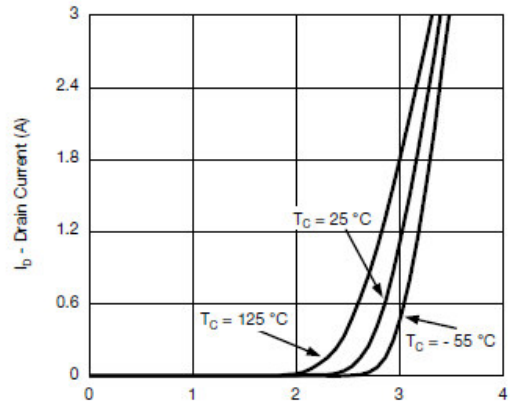
T_A=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = 250uA	100			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = 250uA	1.0		2.0	
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} = ±20V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80V, V _{GS} =0V			1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =85°C			10	
I _{D(on)}	On-State Drain Current	V _{DS} ≥ 5V, V _{GS} = 4.5V	5			A
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V, I _D = 3.0A		280	300	mΩ
		V _{GS} = 4.5V, I _D = 2.0A		290	310	
g _{FS}	Forward Transconductance	V _{DS} = 20V, I _D = 1.5A		2		S
V _{SD}	Diode Forward Voltage	I _S = 1.3A, V _{GS} =0V		0.85	1.2	V
Dynamic						
Q _g	Total Gate Charge	V _{DS} =50V, V _{GS} =4.5V, I _D =1.6A		2.8	5.8	nC
Q _{gs}	Gate-Source Charge			0.75		
Q _{gd}	Gate-Drain Charge			1.4		
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz		200		pF
C _{oss}	Output Capacitance			22		
C _{rss}	Reverse Transfer Capacitance			13		
t _{d(on)}	Turn-On Time	V _{DD} =50V, R _L =39Ω, I _D =1.3A, V _{GEN} =4.5V, R _G =1Ω		25	50	ns
t _r				20	50	
t _{d(off)}	Turn-Off Time			15	30	
t _f				10	25	

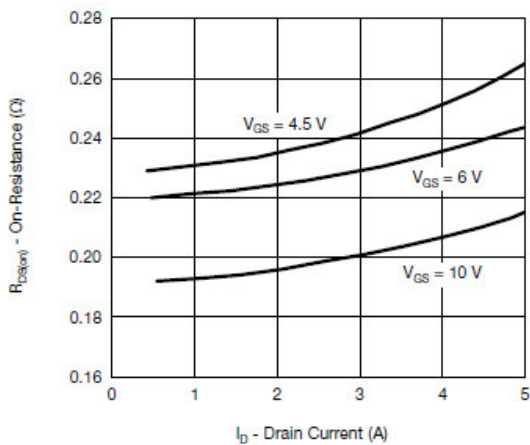
Typical Performance Characteristics



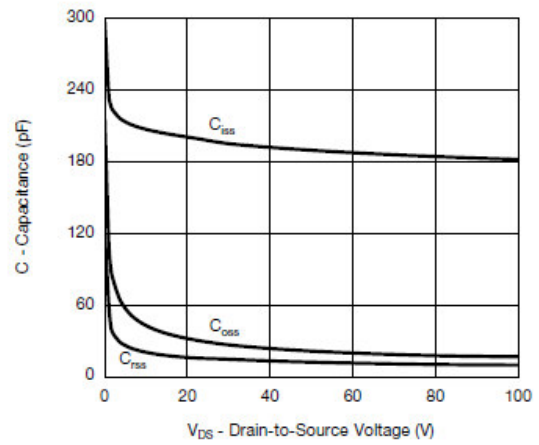
Output Characteristics



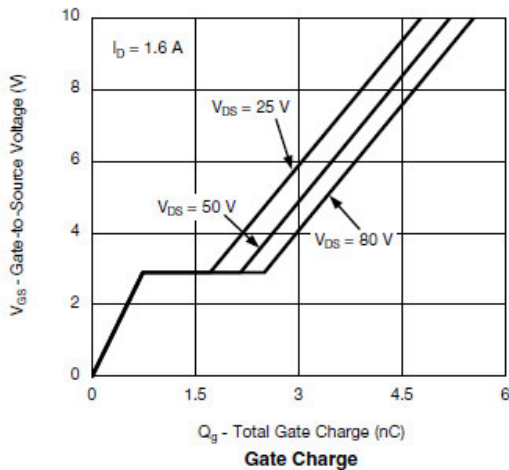
Transfer Characteristics



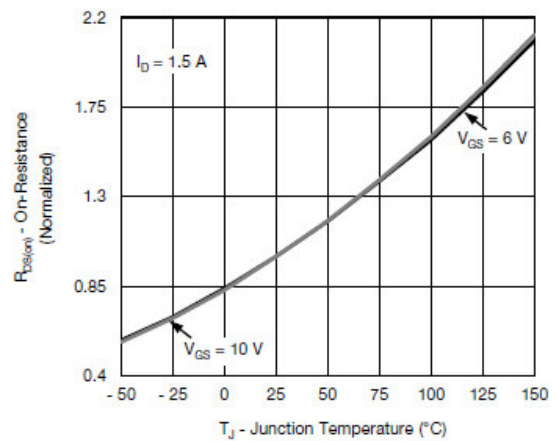
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

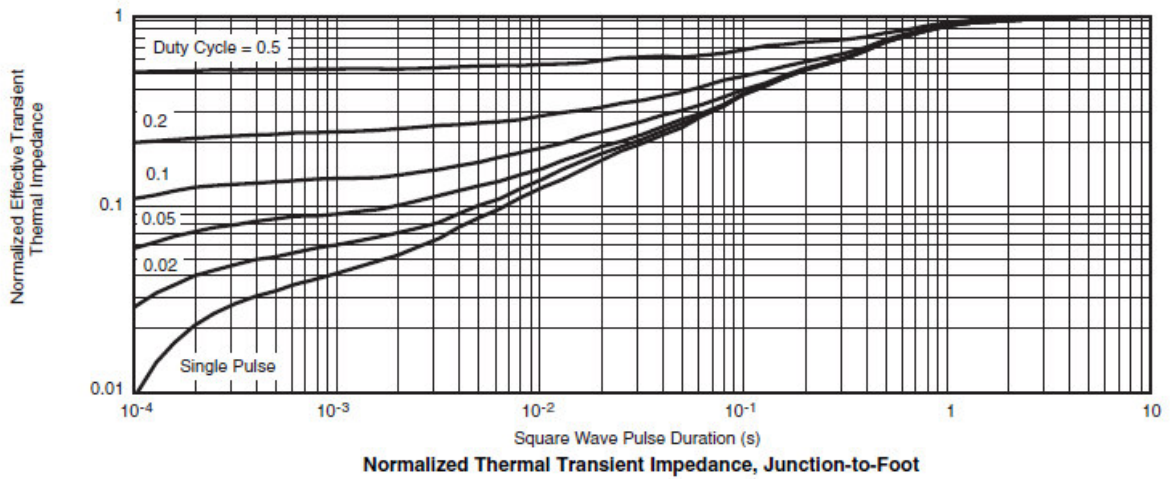
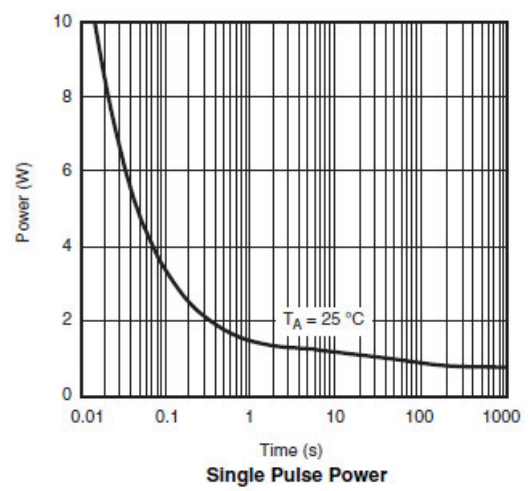
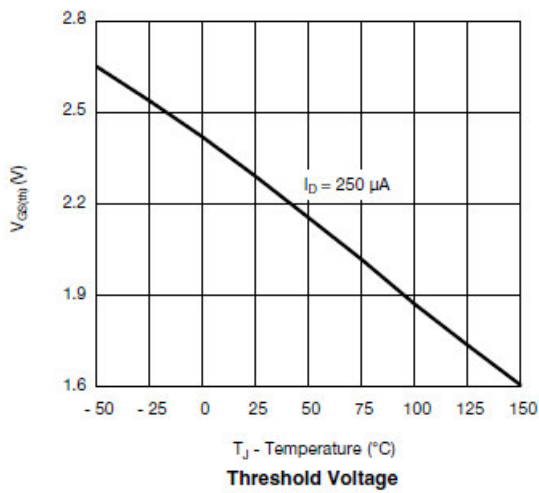
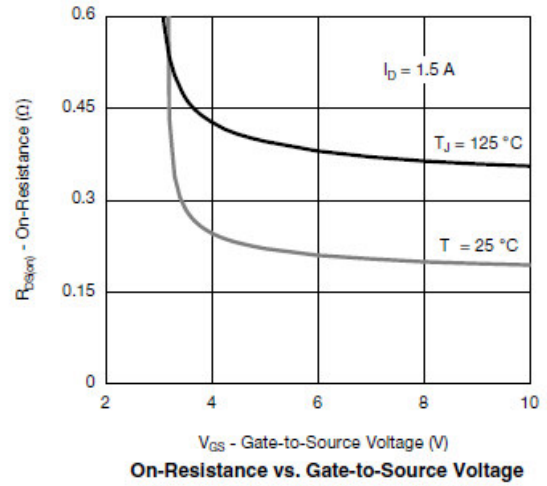
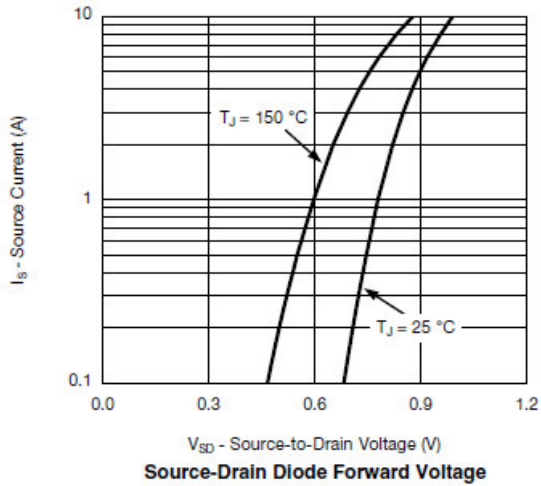


Gate Charge



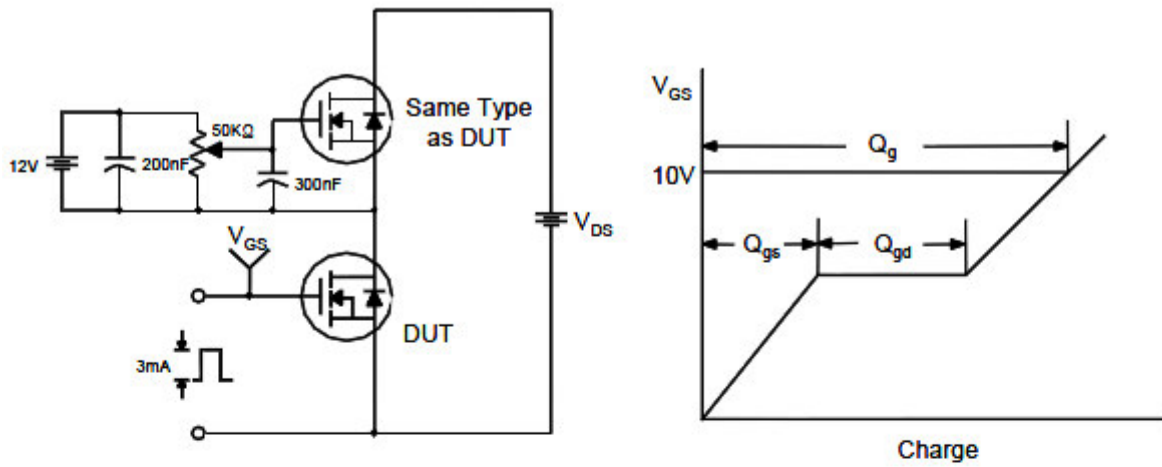
On-Resistance vs. Junction Temperature

Typical Performance Characteristics (continue)

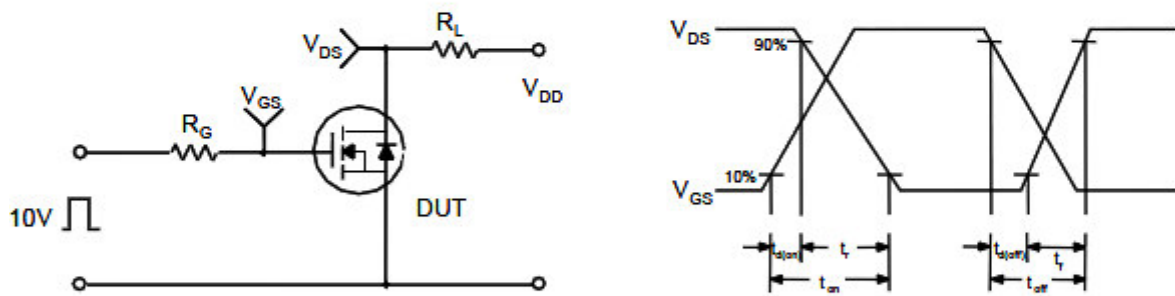


Typical Performance Characteristics (continue)

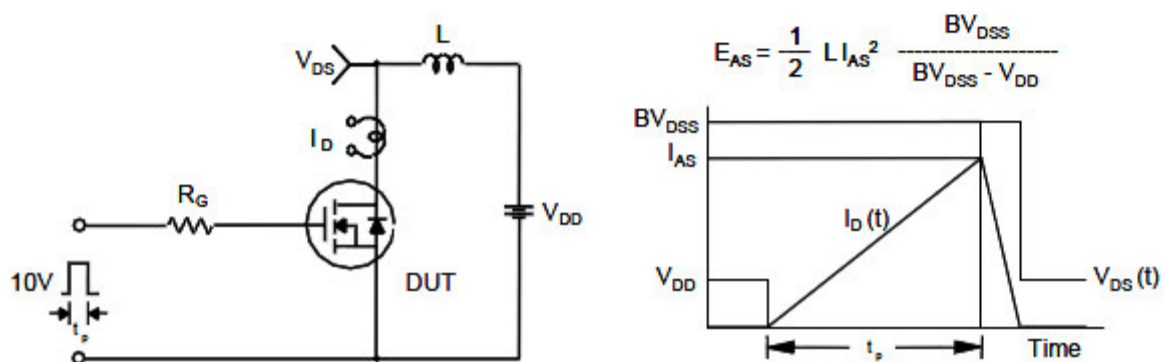
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

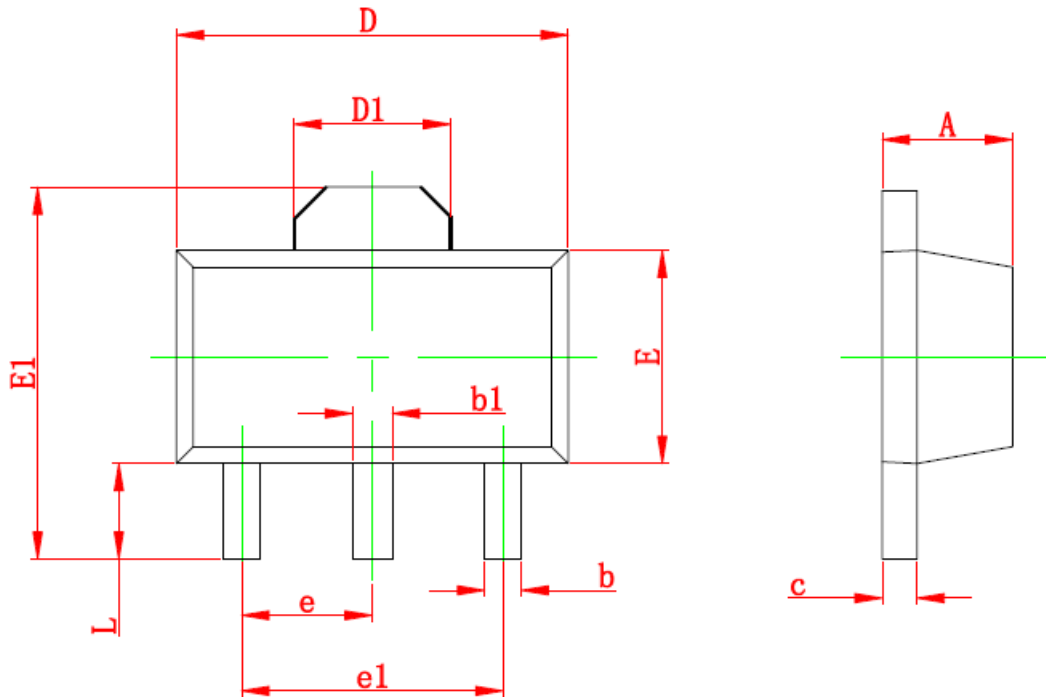


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

SOT-89-3L







Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.197
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 (REF)		0.061 (REF)	
E	2.30	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.50 (TYP)		0.060 (TYP)	
e1	3.00 (TYP)		0.118 (TYP)	
L	0.900 (TYP)	1.200	0.035	0.047



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